PROCESS CP273

Power Transistor

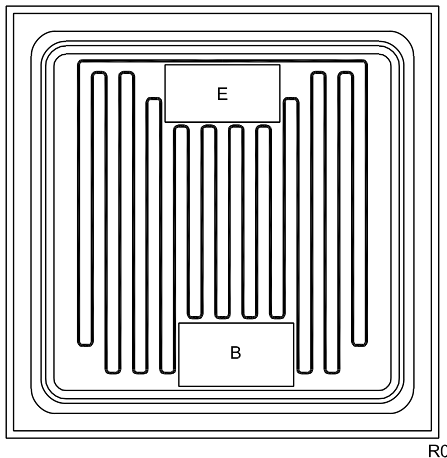
NPN- Silicon Power Transistor Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Die Size	68 x 68 MILS
Die Thickness	8.5 MILS ± 0.6 MILS
Base Bonding Pad Area	17.7 x 10.2 MILS
Emitter Bonding Pad Area	18.1 x 8.9 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ag - 14,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER
2,440

PRINCIPAL DEVICE TYPES
MJE13003

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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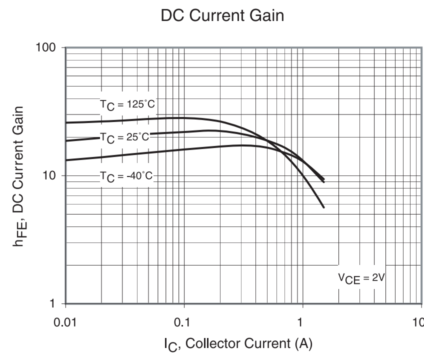
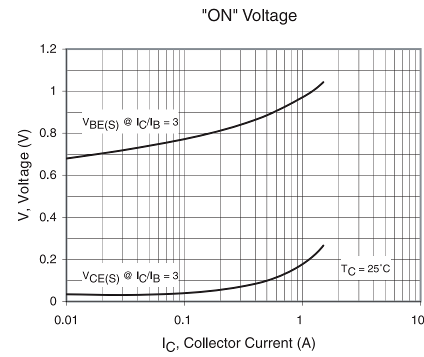
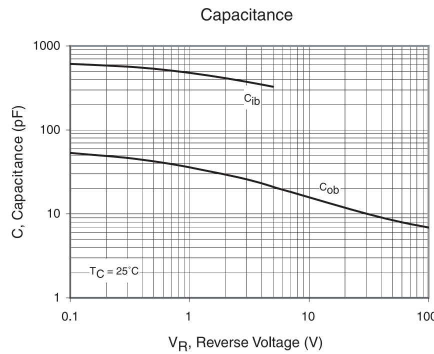
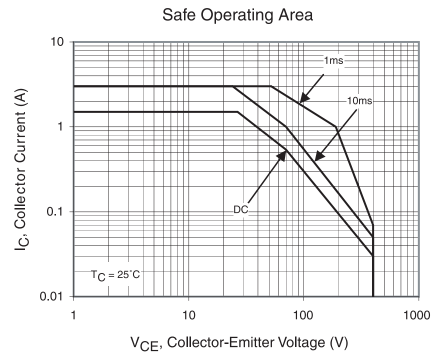
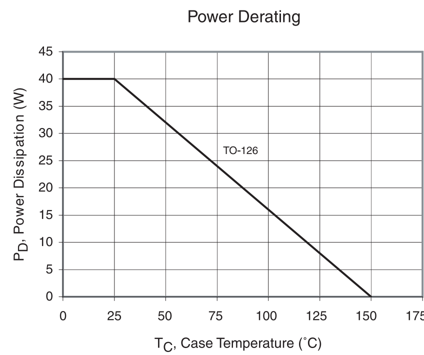
Typical Electrical Characteristics

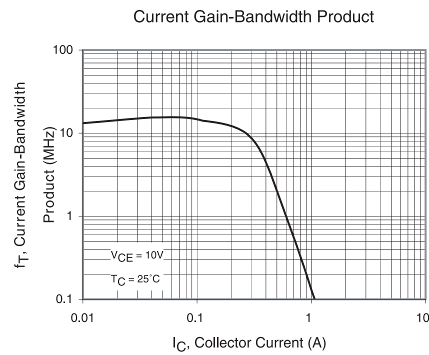












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